

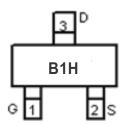


P-Channel Enhancement Mode Power MOSFET

Description

The RM3401Y uses advanced trench technology to provide excellent $R_{\rm DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

Schematic diagram



Marking and pin Assignment



SOT-23-3L top view

General Features

• $V_{DS} = -30V, I_{D} = -4.2A$

 $R_{DS(ON)}$ < 130m Ω @ V_{GS} =-2.5V

 $R_{DS(ON)}$ < 75m Ω @ V_{GS} =-4.5V

 $R_{DS(ON)}$ < 55m Ω @ V_{GS} =-10V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- ■Load switch
- ●Power management
- Halogen-free
- P/N suffix V means AEC-Q101 qualified, e.g:RM3401YV

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
B1H	RM3401Y	SOT-23-3L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	Vgs	±12	V
Drain Current-Continuous	I _D	-4.2	Α
Drain Current-Pulsed (Note 1)	I _{DM}	-30	А
Maximum Power Dissipation	P _D	1.2	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{0JA}	104	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30		-	V

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V		-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-0.7	-1	-1.3	V
	R _{DS(ON)}	V _{GS} =-10V, I _D =-4.2A	-	47	55	mΩ
Drain-Source On-State Resistance		V _{GS} =-4.5V, I _D =-4A	-	56	75	mΩ
		V _{GS} =-2.5V, I _D =-1A		72	130	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-4.2A	-	10	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	\/ - 15\/\/ -0\/	-	880	-	PF
Output Capacitance	C _{oss}	V_{DS} =-15V, V_{GS} =0V, F=1.0MHz	-	105	-	PF
Reverse Transfer Capacitance	C _{rss}	F-1.UIVITZ	-	65	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	7	-	nS
Turn-on Rise Time	t _r	V _{DD} =-15V,I _D =-4.2A	-	3	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10V, R_{GEN} =6 Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Qg		-	8.5	-	nC
Gate-Source Charge	Q_{gs}	V _{DS} =-15V,I _D =-4.2A,V _{GS} =-4.5V	-	1.8	-	nC
Gate-Drain Charge	Q_{gd}		-	2.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-4.2A	-	-	-1.2	V

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature. 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



RATING AND CHARACTERISTICS CURVES (RM3401Y)

Typical Electrical and Thermal Characteristics

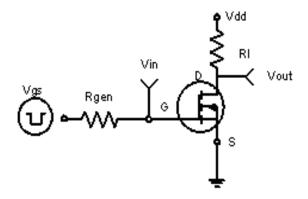
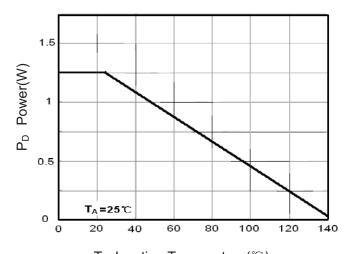
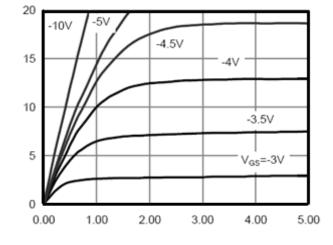


Figure 1:Switching Test Circuit



 T_J -Junction Temperature (°C) Figure 3 Power Dissipation



I_D- Drain Current (A)

Vds Drain-Source Voltage (V) Figure 5 Output Characteristics

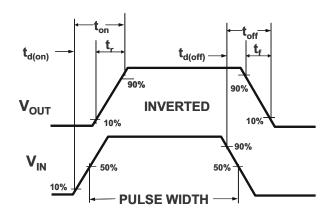
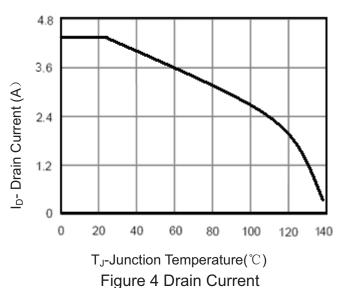


Figure 2:Switching Waveforms



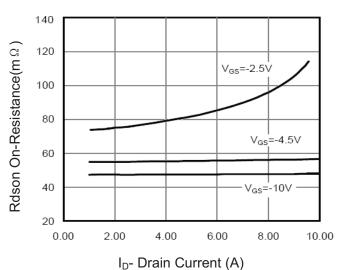
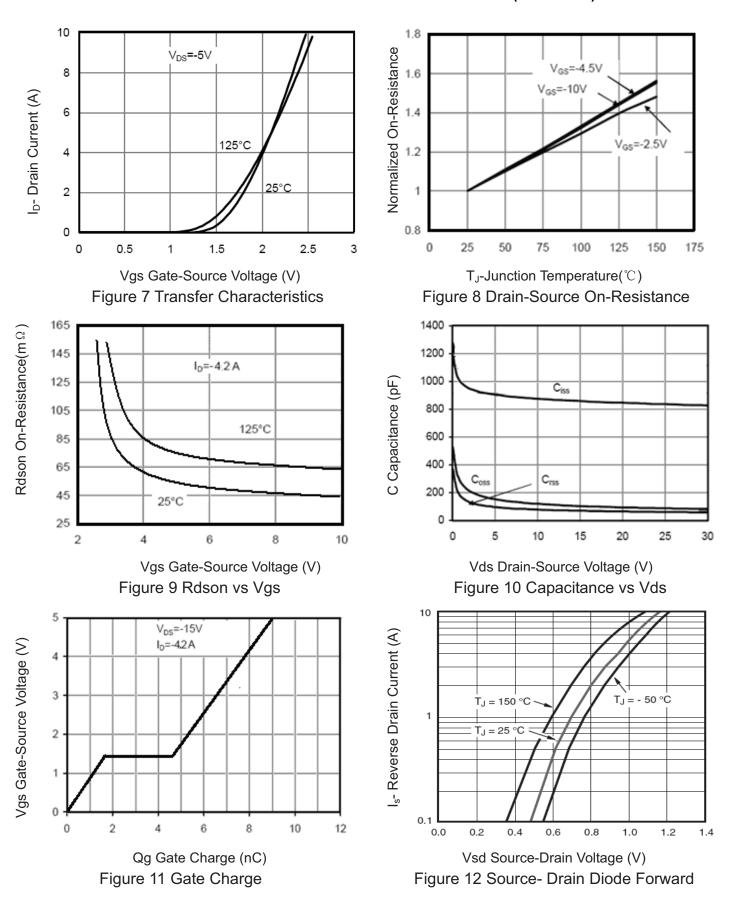


Figure 6 Drain-Source On-Resistance

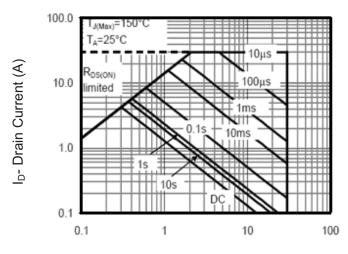


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Vds Drain-Source Voltage (V)
Figure 13 Safe Operation Area

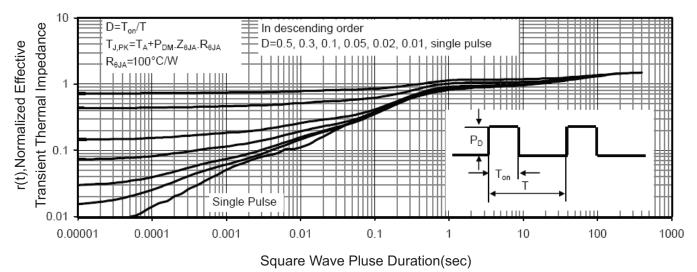
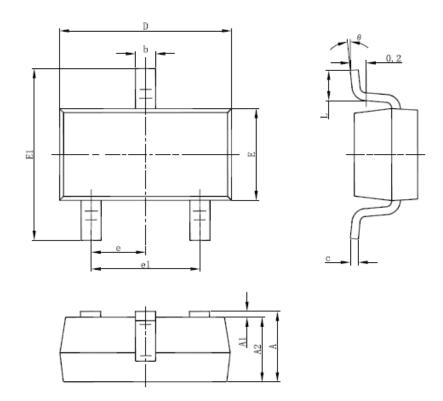


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23-3L Package Information



Symbol	Dimensions Ir	Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950	(BSC)	0.037((BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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